

MOTOROLA SEMICONDUCTOR TECHNICAL DATA

Complementary Silicon Power Transistors

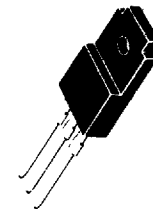
- Designed for use as High Frequency Drivers in Audio Amplifiers
- High Gain, Identified with h_{FE} Classification Letter
- Excellent Frequency Response — $f_T = 100$ MHz

NPN
2SC3298B
PNP
2SA1306B

**SILICON
POWER TRANSISTORS**
1.5 AMPERES
200 VOLTS
20 WATTS

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CB0}	200	V
Collector-Emitter Voltage	V_{CEO}	200	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	1.5	A
Base Current	I_B	0.15	A
Collector Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	20	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$



CASE 221H-01

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	6.25	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 160$ V, $I_E = 0$	—	—	1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5.0$ V, $I_C = 0$	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10$ mA, $I_B = 0$	200	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = 5.0$ V, $I_C = 100$ mA	70	—	240	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500$ mA, $I_B = 50$ mA	—	—	1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5.0$ V, $I_C = 500$ mA	—	—	1.0	V
Current-Gain Bandwidth Product	f_T	$V_{CE} = 10$ V, $I_C = 100$ mA	—	100	—	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10$ V, $I_C = 0$, $f = 1.0$ MHz	—	25	—	pF

NOTE: h_{FE} Classifications; O: 70 to 140 Y: 120 to 240. Units may not be ordered by h_{FE} classification.



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NPN TYPICAL CHARACTERISTICS — 2SC3298B

T-33-01

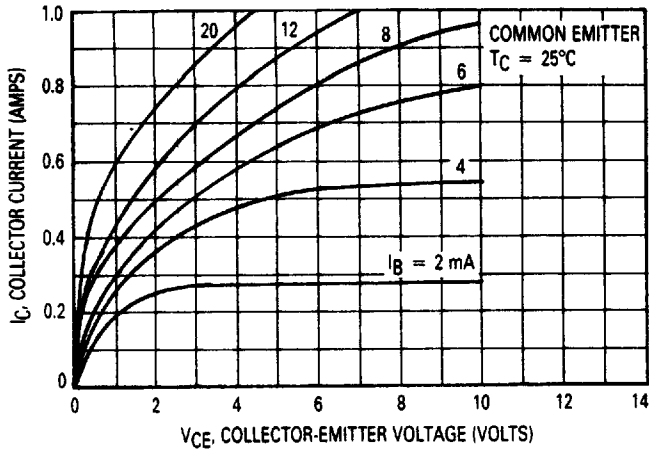


Figure 1. On-Region Characteristics

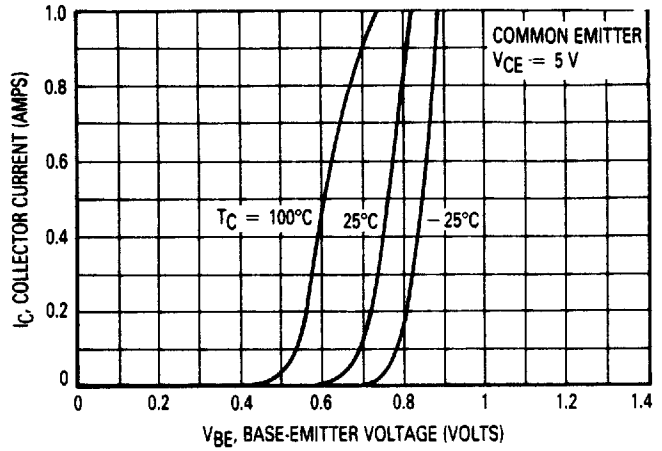


Figure 2. Base-Emitter Voltage

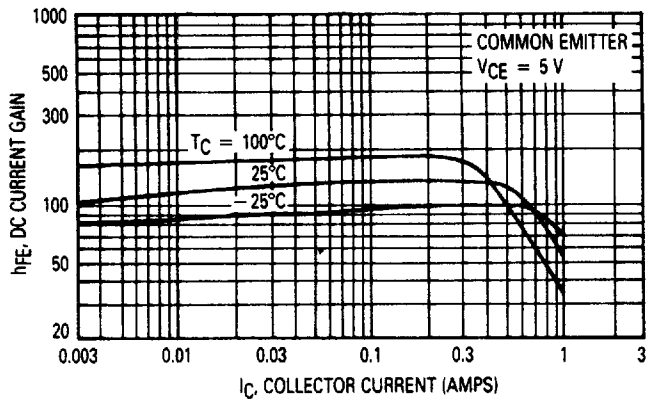


Figure 3. DC Current Gain

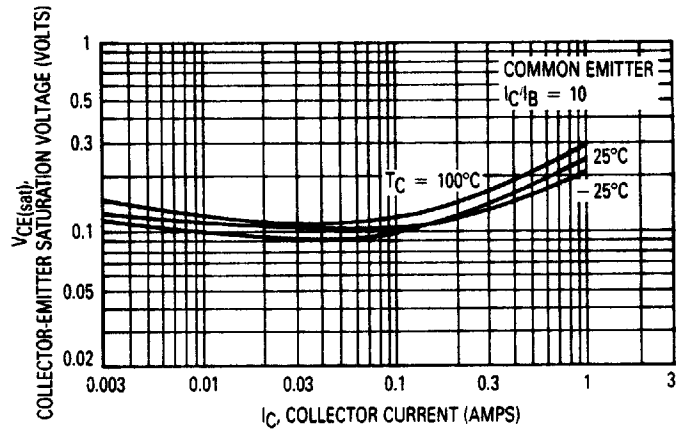


Figure 4. "On" Voltage versus Collector Current

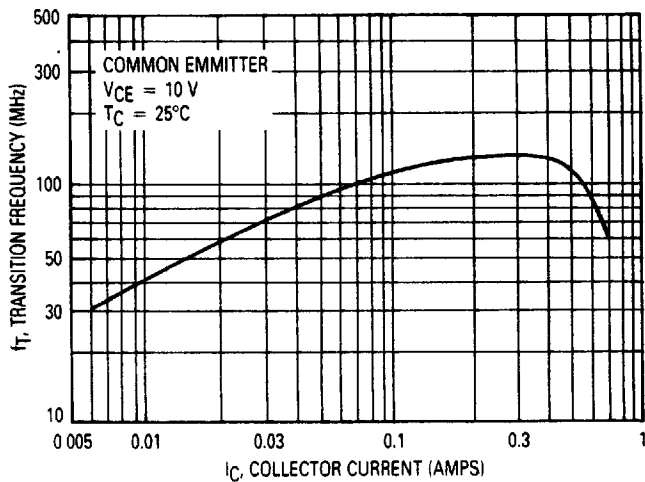


Figure 5. Current-Gain Bandwidth Product

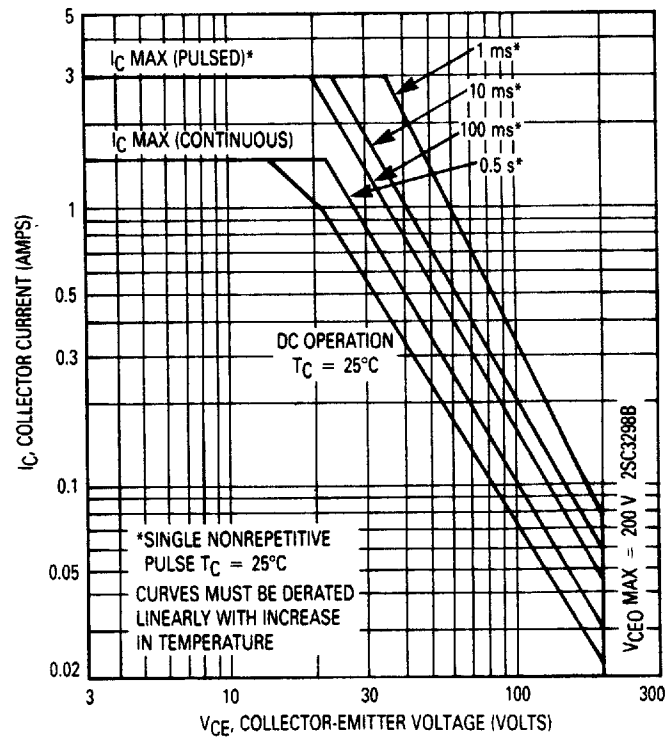


Figure 6. Maximum Forward Bias Safe Operating Area

PNP TYPICAL CHARACTERISTICS — 2SA1306B

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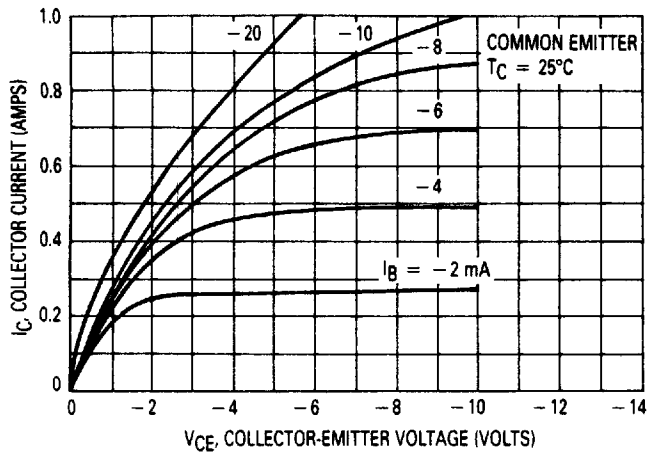


Figure 7. On-Region Characteristics

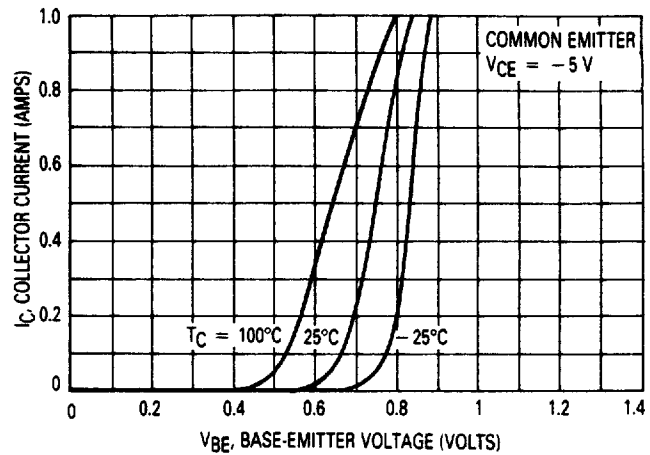


Figure 8. Base-Emitter Voltage

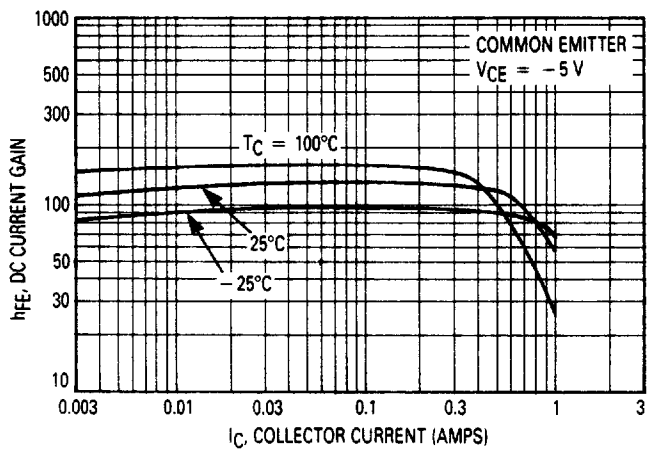


Figure 9. DC Current Gain

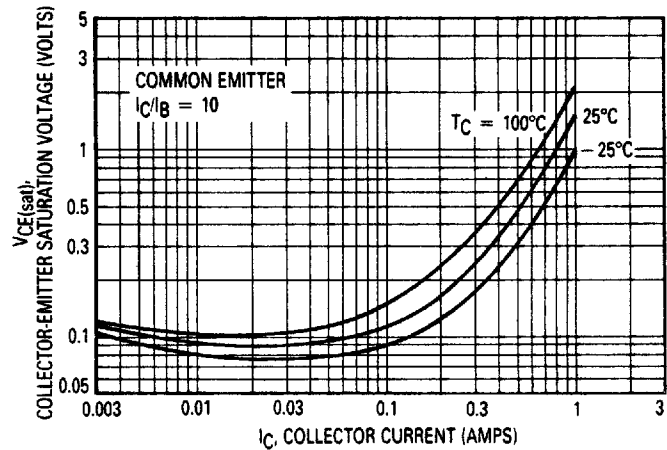


Figure 10. "On" Voltage versus Collector Current

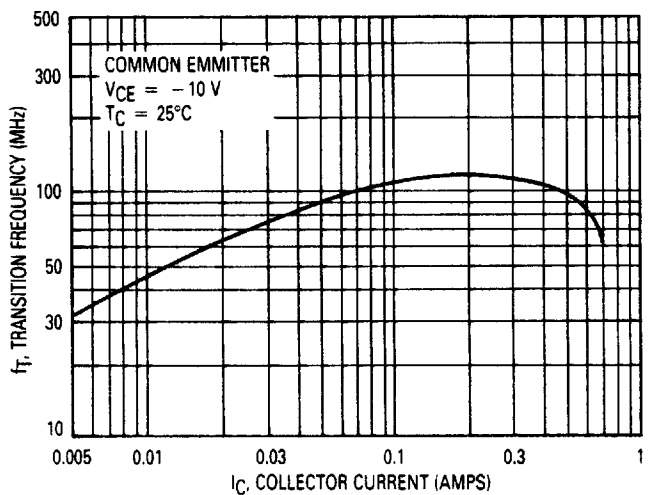


Figure 11. Current-Gain Bandwidth Product

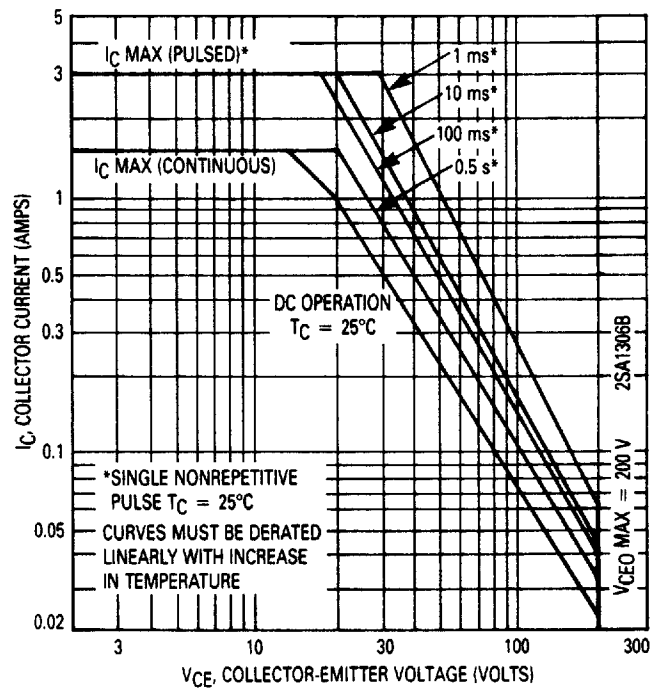
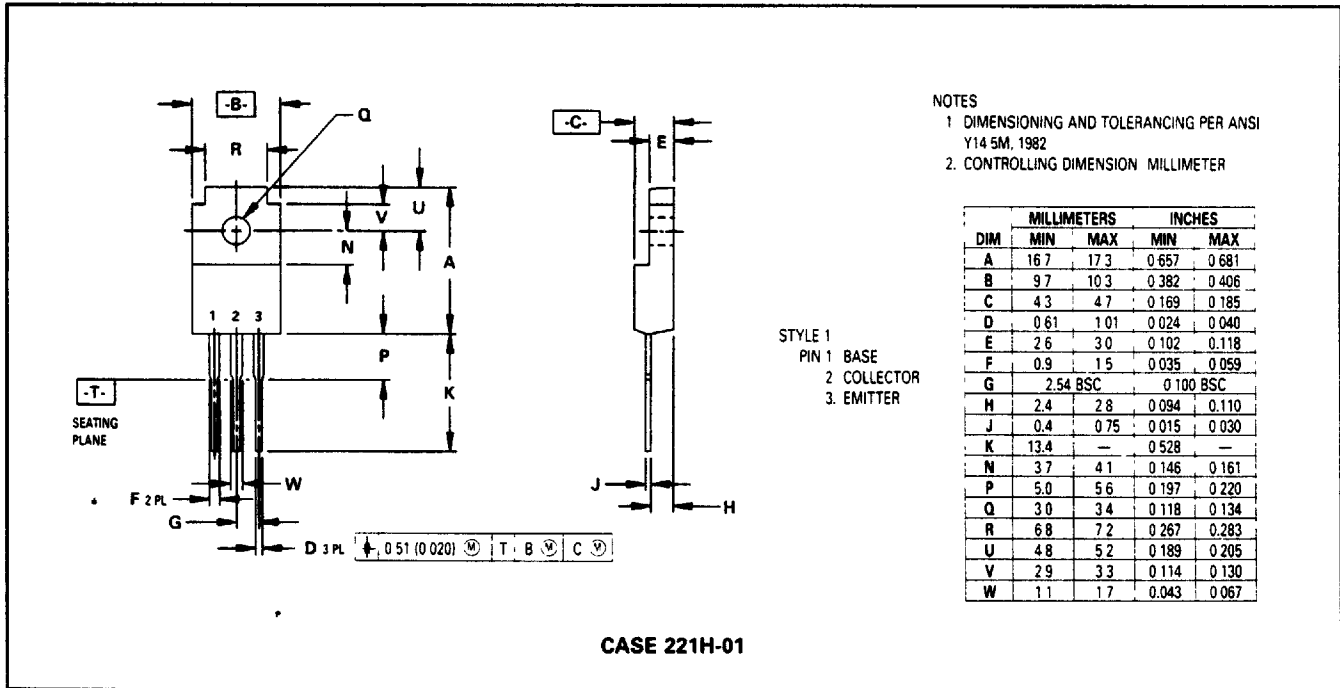


Figure 12. Maximum Forward Bias Safe Operating Area

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